

#### Description

The CSD16340Q3 uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})},$  low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

### **General Features**

 $V_{DS} = 30 V I_D = 120 A$ 

 $R_{DS(ON)}$  < 4.4 m V<sub>GS</sub>=10V

## Application

Battery protection

Load switch

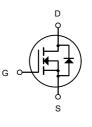
Uninterruptible power supply

### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)		
CSD16340Q3	DFN5X6-8L	HXY MOSFET	5000		
Absolute Maximur	n Ratings (Tc=25℃unle	ess otherwise noted)			
Symbol	Param	neter	er Rating		
Vds	Drain-Source	30	V		
Vgs	Gate-Source Voltage		±20	V	
l₀@Tc=25°C	Continuous Drain Cu	rrent, V <sub>GS</sub> @ 10V <sup>1,6</sup>	120	A	
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1,6</sup>		66	A	
Ідм	Pulsed Drain Current <sup>2</sup>		320	A	
EAS	Single Pulse Avalanche Energy <sup>3</sup>		180	mJ	
las	Avalanche Current		60	A	
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power I	Total Power Dissipation <sup>4</sup>		W	
Тѕтс	Storage Tempe	rature Range	-55 to 150	°C	
TJ	Operating Junction T	emperature Range	-55 to 150	°C	
R <sub>θ</sub> JA	Thermal Resistance	Junction-Ambient <sup>1</sup>	62	°C/W	
Rejc	Thermal Resistanc	e Junction-Case <sup>1</sup>	1.1	°C/W	







N-Channel MOSFET

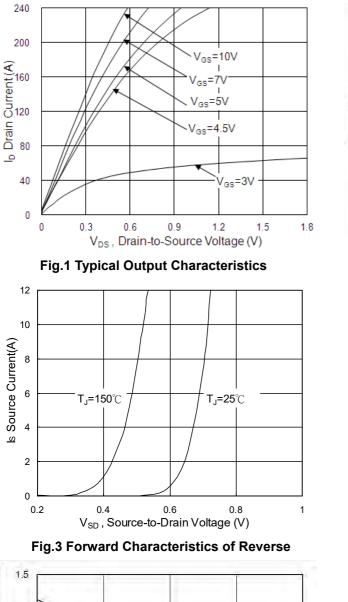


Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
₿Vpss/₽Tj	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.014		V/°C
		V <sub>GS</sub> =10V , I <sub>D</sub> =30A		3.5	4.4	
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =15A		4.6	5.8	mΩ
VGS(th)	Gate Threshold Voltage		1.2		2.5	V
$\mathbb{P}V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	−− V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA		-4		mV/°C
		V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5	uA
lgss	Gate-Source Leakage Current	urce Leakage Current V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA
gfs	Forward Transconductance V <sub>DS</sub> =5V , I <sub>D</sub> =30A			50		S
Rg	Gate Resistance V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz			1.7		Ω
Qg	Total Gate Charge (4.5V)			56.9		
Qgs	Gate-Source Charge	V <sub>DS</sub> =15V , V <sub>GS</sub> =10V , I <sub>D</sub> =15A		13.8		nC
Qgd	Gate-Drain Charge			23.5		
Td(on)	Turn-On Delay Time			20.1		
Tr	Rise Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V ,		6.3		ns
Td(off)	Turn-Off Delay Time	—R <sub>G</sub> =3.3 , I <sub>D</sub> =1A		124.6		
T <sub>f</sub>	Fall Time			15.8		
Ciss	Input Capacitance			4345		
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		340		pF
Crss	Reverse Transfer Capacitance	-		225		
ls	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current			85	A
Vsd	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1.2	V

# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)



## **Typical Characteristics**



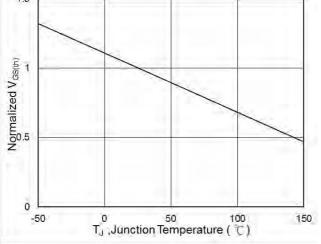


Fig.5 Normalized  $V_{GS(th)}$  v.s T<sub>J</sub>

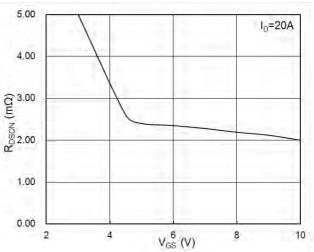


Fig.2 On-Resistance v.s Gate-Source

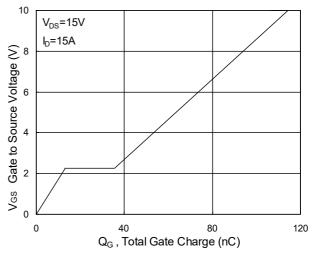


Fig.4 Gate-Charge Characteristics

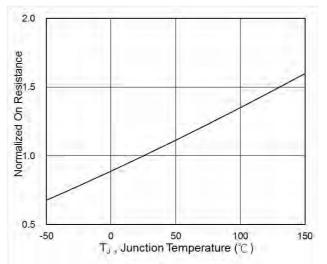


Fig.6 Normalized R<sub>DSON</sub> v.s T<sub>J</sub>



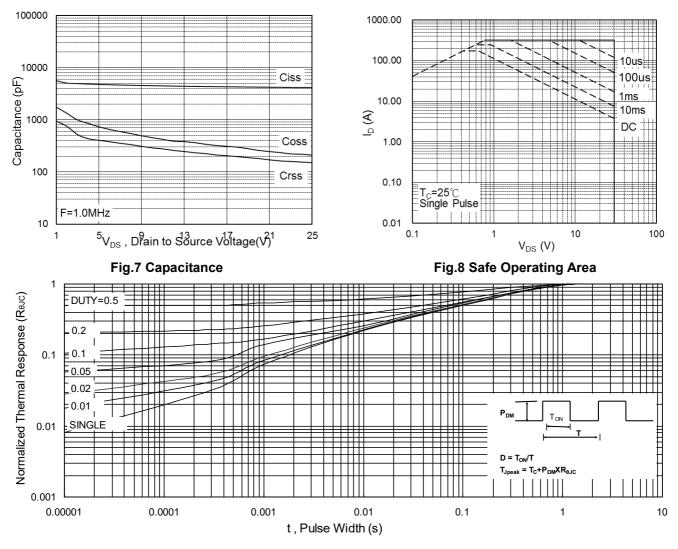


Fig.9 Normalized Maximum Transient Thermal Impedance

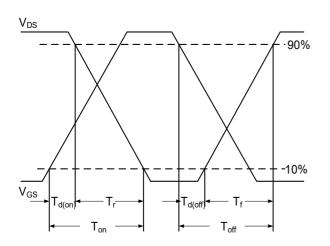
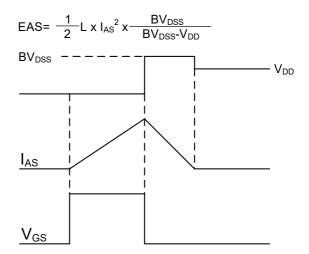
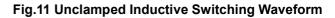


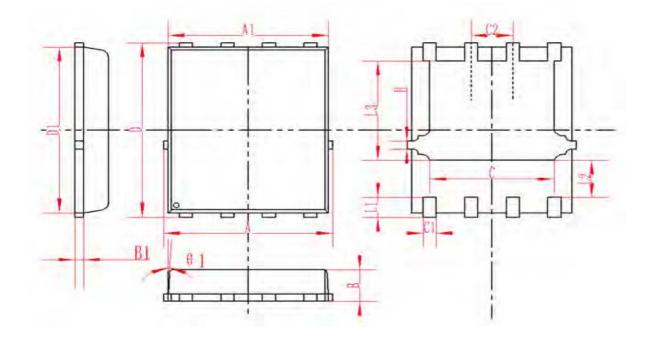
Fig.10 Switching Time Waveform







# DFN5X6-8L Package Information



SYMBOL	MM			INCH			
	MIN	NOM	MAX	MIN	NOM	MAX	
А	5.3	5.5	5.7	0.208	0.216	0.224	
A1	5.1	5.2	5.3	0.2	0.204	0.209	
D	5.98	6	6.02	0.235	0.236	0.237	
D1	5.85	6.05	6.25	0.23	0.238	0.246	
В	0.85	0.95	1.05	0.033	0.037	0.041	
B1	0.254REF			0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159	
C1	0.35	0.4	0.45	0.014	0.016	0.018	
C2	1.27TYP			0.5TYP			
θ1	8°	10°	12°	8°	10°	12°	
L1	0.63	0.64	0.65	0.025	0.025	0.026	
L2	1.2	1.3	1.4	0.047	0.051	0.055	
L3	3.415	3.42	3.425	0.134	0.135	0.135	
Н	0.24	0.25	0.26	0.009	0.010	0.010	



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